

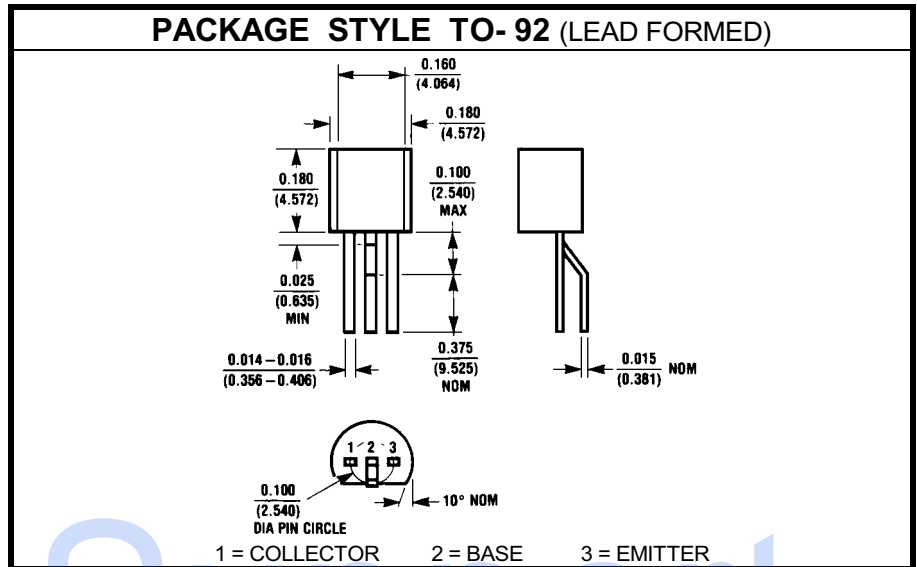
SILICON PNP TRANSISTOR

DESCRIPTION:

The **2N3645-92** is Designed for General Purpose Amplifier and Switching Applications.

MAXIMUM RATINGS

I_C	500 mA
V_{CE}	-60 V
P_{DISS}	700 mW @ $T_C = 25^\circ C$
T_J	-55 °C to +125 °C
T_{STG}	-55 °C to +125 °C
θ_{JC}	143 °C/W


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10 \text{ mA}$		-60V			
BV_{CBO}	$I_C = 100 \mu A$		-60V			
I_{CES}	$V_{CE} = -50 \text{ V}$ $V_{CE} = -50 \text{ V}$	$V_{BE} = 0 \text{ V}$ $V_{CE} = -50 \text{ V}$			35 2.0	nA μA
BV_{EBO}	$I_E = 10 \mu A$		-5.0V			
h_{FE}	$V_{CE} = -10 \text{ V}$	$I_C = 100 \mu$ $I_C = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}$ $I_C = 50 \text{ mA}$ $I_C = 150 \text{ mA}$ $I_C = 300 \text{ mA}$	40 80 100 115 100 20		300 300	---
$V_{CE(SAT)}$	$I_C = 150 \text{ mA}$ $I_C = 300 \text{ mA}$	$I_B = 15 \text{ mA}$ $I_B = 30 \text{ mA}$			-0.4 -1.0	V
$V_{BE(SAT)}$	$I_C = 150 \text{ mA}$ $I_C = 300 \text{ mA}$	$I_B = 15 \text{ mA}$ $I_B = 30 \text{ mA}$			-1.3 -2.0	V
f_t	$V_{CE} = -20 \text{ V}$	$I_C = 20 \text{ mA}$	$f = 100 \text{ MHz}$	2.0		
C_{ob}	$V_{CB} = -10 \text{ V}$		$f = 1.0 \text{ MHz}$		8.0	pF
C_{ib}	$V_{EB} = -0.5 \text{ V}$		$f = 1.0 \text{ MHz}$		25	pF
t_{on}	$I_C \cong 300 \text{ mA}$	$I_{B1} \cong 30 \text{ mA}$			40	nS
t_{off}	$I_C \cong 300 \text{ mA}$	$I_{B1} = I_{B2} \cong 30 \text{ mA}$			100	nS